

Andrew J Green

List of Publications by Year in descending order

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687363

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1141
citing authors

#	ARTICLE	IF	CITATIONS
1	3.8-MV/cm Breakdown Strength of MOVPE-Grown Sn-Doped β -Ga ₂ O ₃ MOSFETs. IEEE Electron Device Letters, 2016, 37, 902-905.	3.9	468
2	Enhancement-mode Ga ₂ O ₃ wrap-gate fin field-effect transistors on native (100) β -Ga ₂ O ₃ substrate with high breakdown voltage. Applied Physics Letters, 2016, 109, .	3.3	298
3	Recessed-Gate Enhancement-Mode β -Ga ₂ O ₃ MOSFETs. IEEE Electron Device Letters, 2018, 39, 67-70.	3.9	187
4	β -Gallium oxide power electronics. APL Materials, 2022, 10, .	5.1	184
5	Highly conductive homoepitaxial Si-doped Ga ₂ O ₃ films on (010) β -Ga ₂ O ₃ by pulsed laser deposition. Applied Physics Letters, 2017, 111, .	3.3	128
6	Lateral β -Ga ₂ O ₃ field effect transistors. Semiconductor Science and Technology, 2020, 35, 013002.	2.0	85
7	High pulsed current density β -Ga ₂ O ₃ MOSFETs verified by an analytical model corrected for interface charge. Applied Physics Letters, 2017, 110, .	3.3	75
8	ScAlN/GaN High-Electron-Mobility Transistors With 2.4-A/mm Current Density and 0.67-S/mm Transconductance. IEEE Electron Device Letters, 2019, 40, 1056-1059.	3.9	63
9	RF Power Performance of Sc(Al,Ga)N/GaN HEMTs at Ka-Band. IEEE Electron Device Letters, 2020, 41, 1181-1184.	3.9	41
10	Si content variation and influence of deposition atmosphere in homoepitaxial Si-doped β -Ga ₂ O ₃ films by pulsed laser deposition. APL Materials, 2018, 6, 101102.	5.1	40
11	Thin channel β -Ga ₂ O ₃ MOSFETs with self-aligned refractory metal gates. Applied Physics Express, 2019, 12, 126501.	2.4	35
12	Electrical and chemical analysis of Ti/Au contacts to β -Ga ₂ O ₃ . APL Materials, 2021, 9, 061104.	5.1	23
13	Homoepitaxial β -Ga ₂ O ₃ transparent conducting oxide with conductivity $\sigma = 2323 \text{ S cm}^{-1}$. APL Materials, 2021, 9, .	5.1	22
14	Thermally-Aware Layout Design of β -Ga ₂ O ₃ Lateral MOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 1251-1257.	3.0	11
15	Ionic Metal-Oxide TFTs for Integrated Switching Applications. IEEE Transactions on Electron Devices, 2016, 63, 1921-1927.	3.0	9
16	Scaled T-Gate β -Ga ₂ O ₃ MESFETs With 2.45 kV Breakdown and High Switching Figure of Merit. IEEE Electron Device Letters, 2022, 43, 1307-1310.	3.9	8
17	The effectiveness of heat extraction by the drain metal contact of β -Ga ₂ O ₃ MOSFETs. , 2021, , .		1